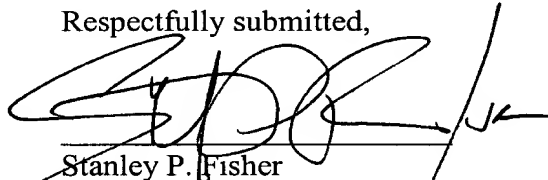


REMARKS

Applicant has amended claim 6 and added claims 11, 12 and 13, amended claim 7 and added claims 14, 15 and 16, amended claim 8 and added claims 17, 18 and 19, added claims 20, 21 and 22, amended claim 10 and added claims 23, 24, 25 and 26. Applicant has amended the claims in order to remove the multiple dependencies contained therein in accordance with standard U.S. practice, thereby reducing the basic filing fee. No new matter has been added to the application as a result of this amendment.

In view of the above amendments and Applicant's comments stated herein, Applicant respectfully requests an early and favorable action on the merits.

Respectfully submitted,



Stanley P. Fisher

Registration Number 24,344

REED SMITH HAZEL & THOMAS LLP

3110 Fairview Park Drive
Suite 1400
Falls Church, Virginia 22042
(703) 641-4200

JUAN CARLOS A. MARQUEZ
Registration No. 34,072

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MARKED-UP CLAIMS

a gate electrode of each of the second thin-film transistors is made of a material different than a wiring layer or electrode and electrically connected to the wiring layer or electrode;

the gate electrode of the first thin-film transistor is made of the same material as that of each of the second thin-film transistors; and

the gate signal line is made of the same material as the wiring layer or electrode.

6. The active matrix display device according to ~~any one~~ of claims 1 ~~to 4~~, wherein the gate signal line is made of aluminum.

7. The active matrix display device according to ~~any one~~ of claims 1 ~~to 4~~, wherein a semiconductor layer of the first thin-film transistor and/or each of the second thin-film transistors is made of polysilicon.

8. The active matrix display device according to ~~any one~~ of claims 1 ~~to 4~~, wherein metal layers are formed on a drain region and a source region, respectively, of the first thin-film transistor and/or each of the second thin-film transistors, and portions of the respective metal layers are exposed through respective contact holes that are formed through a passivation film that covers the thin-film transistor.

9. The active matrix display device according to claim 8, wherein the metal layers are formed at the same time as a